6 November 2020 11:38 1) Revised Performance Order of PART-B Assignments prescribed by SPPU 2) Hands-On Learning of TOOL: MICROWIND 3.1 (LAYOUT EDITOR) MICROWIND VS MultiSim , PROTEUS ✓ Invoking the Tool from HARD-DISK → Tool Workspace Target Technology ✓➤ Tool GUI Correct Starting Point for Drawing LAYOUT Enlisting STEPS to DRAW Layout of CMOS INVERTER Demonstrating STEPS Enlisted above Observing Various Simulations (Vin-Vo vs t, Vo vs Isupply, Vo vs Vin) Noting DYNAMIC Power Dissipation, P(dynamic) of Circuit Mathematical Model for P(dynamic) Seeing Effect of Changing fclk, C(load) & Vdd on P(dynamic) 1 List of PART-B Assignments: - Draw Layouk - Simulate - Obseive the opps - Analyze & Conclude 1 Combinational circults 1 (a) CMOS Inverter 2 (b) CMOS NAND CTAte 3 (c) CMOS NOR Gate 4 (d) CMOS AND OR Gate (e) CMOS (f) CMOS Half-Adder > 1 EXOR= A.B + A.B > 22 mosfels * I AND = A.B => 6 mosfels 2:1 Mux using TG Logic 1-bit SRAM Memory (BT Cell) Microwind Vs Mulbisim, Proteus Similarity -- All 3 are Electronics CAD Tools Multisim, Proteus (Circuit schematic Editors)

> Workspace Represents a PCB - All Dimensions are in cms/mm

Difference -

- MicroWind is a-VLSI (AD Tool
 BackEnd Tool
 Making ICs Layout Edilor
 - Workspace of uwind Represent a Si-Water
 - All dimensions are in nm

$$\begin{array}{ccc}
5 & \text{lumbda} & 5 & \lambda = 0.250 \, \mu\text{m} \\
0.250 & \mu & = 250 \, \text{nm} \\
& \lambda = 50 \, \text{nm}
\end{array}$$

Targel= Technology = 2x = 100 nm

Foundry

Node

Process

Min. Feature size

Channel length (L)

λ= 50 nm

- (*) Calculating Foundry value from Scale gives

 us " 2λ " \Rightarrow Fabricated Channel length (L)
 - ⊕ Rule file ⇒ Available channel length (Left)

Leff =
$$L - 2(\Delta L)$$

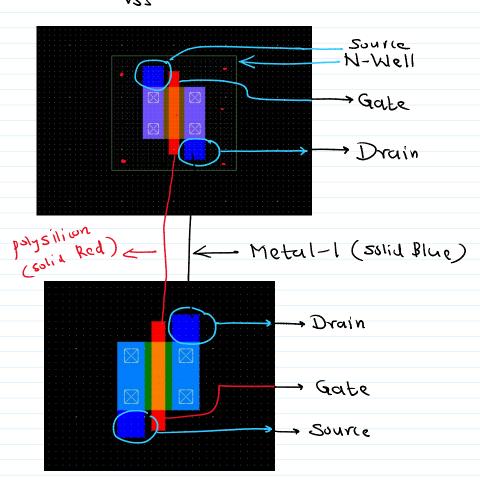
 ΔL : Width of Depletion Regions
 $\otimes S - B \neq D - B$

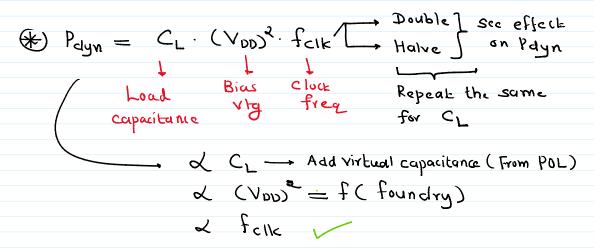
(CSP for ED ⇒ Block Diagram (on papel)

(CSP for AB ⇒ TT/FT/Bool. expin/Stak-Diagram

(x) CSP for Making Any Layout in uwind is (Transistor-Level schematic (circult) of the system (on paper) (MUSFETS) (*) STEPS for Drawing Layout of CMOS Inverter: 1) Draw the TLS of CMOS Invester on paper. (2) Terminalise the circuit Diagram (Indicate D, G, S) (of Layers) 3) Place all Musfets into Workspace (using Mos Generator in Pol) (Hori. / vert. / Rotate) [Stretch/move) to enable easy connectivity betin their Terminals (5) Connect Terminals of Mosfets to each other as perpoint-2 6) Apply + YDD & -Vss to the system (7) Polarise all N-wells in your circuit]- Ensures that Connect N-well to +VDD I floating - There is No Electrical Rule Error (8) Apply all I/p signals as per point-a (3) Define all 0/p Nudes as per point-2 (10) Perform DRC (Design Rule Check) (11) Simulate, Observe O/ps, Analyse, Conclude STEP-1:- TLS of CMOS Inverter. STED- 2: - Terminalised

Q N





(★) A new; but Standard Value of +VDD can be used only by Changing the foundry

File → Select foundry

(Menu)

File - Select foundry (Menu)

* Which layers to be used connecting Terminals?

 $D \leftrightarrow D$ $S \leftrightarrow S$ $D \leftrightarrow S$ $Q \leftrightarrow Q \rightarrow Polysilian$

⊕ O/P is always available

on Metal-1 Layer

on Gak Terminal; honce

- Using DSCH Topon Tool by clicking DSCH3-exe inside Tool's folder
 - 1) Draw Either Transistor/Gate-Level Schematic using SYMBOL LIBRART
 - Solf-explanatory name (* sch)
 - 3 Simulate the schematic & verify functionality.
 - 4) Generate "Verilog File" from FILE → Make Verilog File
 - (5) Change Default: File Name (example.sch) to selfexplanatory.
 - (6) Click ok
 - (7) Open MICROWIND Tool
 - 8) Go To (Menu) COMPILE → Compile Verilog File
 - (9) Browse to your destination folder of Verilog File
 - (10) Select File Type to "All Files (** *)
 - (1) Select your" Verilog code" contained * txt file
 - (R) Click "COMPILE"
 - (13) Click "Back to Editor"
 - (4) Simulate